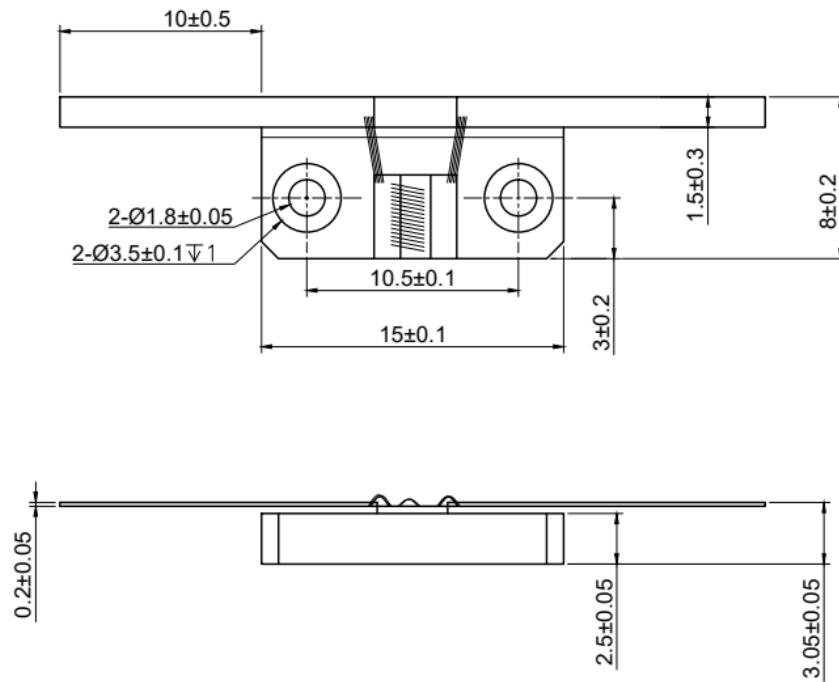


808nm~810nm 10W E-mount Laser Diode | FAC Optional | Square Beam Optional
808nm Laser Diode| High Power LD| 10W Power| E-mount Package
RWSLD-808-010-E

808nm Laser Diode		10W/E-mount		
PARAMETER	SYMBOL	VALUE	UNIT	
Reverse Voltage	V_r	2.0	V	
Operating Temperature	T_{op}	+10~+30	°C	
Storage Temperature	T_{stg}	-20~ +80	°C	
Lead soldering temperature (10 sec.)	T_{is}	260	°C	
Features: <ul style="list-style-type: none"> 808nm Multimode E-mount Package FAC Lens Optional 				
Applications: <ul style="list-style-type: none"> Medical Laser Treatment Laser Pumping Others 				
Specifications		RWSLD-808-010-E		
		Min	Type	Max
Center Wavelength@25°C		808nm ± 10nm		
Spectral Width (FWHM)			3.0nm	
Output Power		----	10W	----
Emitter Area		----	200x1µm	----
Beam Divergence (FWHM)		----	30° _⊥ x 8° _{//}	----
Temperature Coefficient of Wavelength		----	0.3nm / °C	----
Slope Efficiency		----	1.05W/A	----
Threshold Current (Typ.)		----	1.5A	2.0A
Operating Current (Typ.)		----	11.0A	12.0A
Operating Voltage		----	1.9V	2.4V
Package Style		E-mount		
Recommended Operating Temperature		25°C		

E-mount Package View

mm



**Electrically shorten LD module and store in non-extreme conditions.
Suggest using the constant current power supply.**

